

Elastic Softening in Synthetic Diamonds

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This study reveals a novel phenomenon demonstrating the softening of synthetic diamonds when cooled to very low temperatures below 1 K. Herein, we argue that this elastic softening can be attributed to the effect of electric-quadrupole degrees of freedom of the dangling bonds in the neutral single-atom vacancies of carbon. We present the results of ultrasonic investigations of single-crystalline synthetic diamonds, namely type-IIa (colorless) and Ib (yellow) diamonds grown by high-pressure-high-temperature synthesis as well as type-IIa diamond grown by chemical vapor deposition. We observe a magnetic-field-insensitive softening of the elastic constant C_{44} in all samples at low temperatures below 1 K. Our results strongly suggest a ppb level concentration of neutral single-atomic vacancies in all investigated diamonds. Our findings open new avenues for the quantitative determination of single neutral vacancies in non-irradiated diamonds, an important information needed for their potential application for quantum technology and next-generation semiconductor devices.

Since ancient times, impurities and defects in diamonds have been considered as crucial criteria for appraising jewelry. Recently, the development of synthesis methods for artificial diamonds is of interest not only for semiconductor industry [1], but also for the study of the quantum properties of defects and possibilities for potential applications [2–5]. Particularly, quantum states of defects arising from atomic vacancies in diamonds are considered promising for application in solid-state quantum sensors in the broad range from life to materials science [6–9]. Such states also pave the way from fundamental physics to quantum technology, including quantum computation and quantum communication [10–15]. Quantum-technology studies based on diamonds have primarily utilized commercially available synthetic diamonds prepared through high-temperature-high-pressure (HPHT) or chemical vapor deposition (CVD) methods. Although numerous researchers have investigated how defect centers originating from atomic vacancies with adjacent nitrogen atoms, called NV centers, can be grown and engineered [16–19], studies comparing and evaluating the defect-center states in diamonds are scarce. In particular, whether the synthetic diamonds used as substrates for quantum devices contain atomic vacancies and to which amount has not yet been explored.

During the synthesis process, the generation of single-atom vacancies on the ppm to ppb level is thermodynamically inevitable [20] and should be well controlled in quantum technologies. Previous studies have primarily reported ppm-level concentrations of neutral single vacancies V_0 on irradiated diamond samples [21–23]. However, the details of the existence and density of such vacancies (shown in Fig. 1) in non-irradiated synthetic di-

amonds have not yet been elaborated. Thus, reliable determination of V_0 concentrations at the ppb level and investigation of vacancy properties are crucial for the rational development of novel quantum technologies. Here, we report the successful determination of the neutral single vacancy concentration in the order of ppb by quantitative analysis of the elastic softening based on the quadrupolar susceptibility [20]. Herein, the elastic “softening” refers to a decrease in the elastic stiffness constant. We further demonstrate that ultrasonic measurements at very low temperatures are a robust tool for detecting and studying neutral single vacancies in single-crystalline diamond.

Diamond has a cubic crystal structure (O_h^7 , $Fd\bar{3}m$, No.227) with lattice constant $a = 3.567\text{\AA}$ [24], as schematically shown in Fig. 1 (top). The sp^3 orbitals of carbon with the outermost electron configuration $(2s)^2(2p)^2$ covalently bond to each other and thereby form the diamond structure, resulting in one of the hardest materials on earth. Diamonds exhibit different colors depending on the amount and type of impurities in the crystal. A yellow color is indicative for dominant nitrogen impurities (type Ib), whereas blue-colored diamond indicates the presence of boron as primary impurity (type IIb). There exist two types of colorless diamonds: type Ia, which contains nitrogen atoms in dimer form, and type IIa, which contains only a few impurities. HPHT flux and CVD methods are utilized for synthesizing type-IIa crystals. Recently, the technologies for synthesizing large high-quality single-crystalline diamonds have been significantly improved.

In an earlier study, Goto and coworkers successfully detected V_0 vacancies [25] in single-crystalline Si through ultrasound. Indeed, Goto and coworkers observed a low-

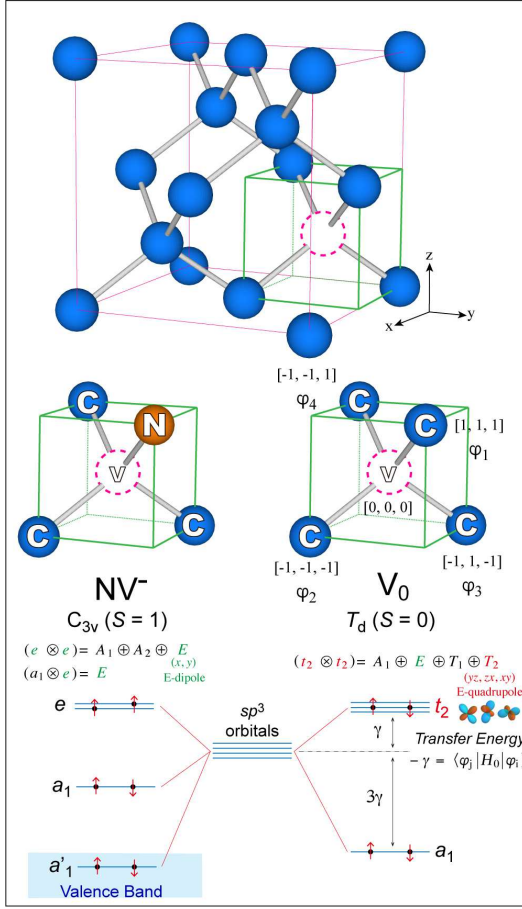


FIG. 1. (Top) Diamond crystal structure with a single atomic vacancy in a unit cell. (Middle) Schematic illustrations of the NV^- center (left) and V_0 (right). Considering a single-atomic vacancy V_0 , in which one carbon atom is missing, we assume $\varphi_1, \varphi_2, \varphi_3$, and φ_4 as the wavefunctions of the four-fold degeneracies of equivalent sp^3 orbitals formed by the dangling bonds [25], which are numbered in the direction of the nearest neighbors from the center of the tetrahedron. (Bottom) Electron occupation of the ground-state molecule orbitals configuration of (left) a negatively charged center (NV^-) and (right) a neutral vacancy (V_0). The red arrows represent electron spins, and their arrangement. The sp^3 orbital splits owing to the symmetry lowering caused by each defect. The direct sum equation demonstrates the symmetry of the electronic degrees of freedom of the direct product space of each degenerate quantum state.

temperature softening for some acoustic modes in Si at cryogenic temperatures [20, 26–32]. Despite significant advancements of crystal-growth techniques and of the electronic properties of large-diameter Si wafers in semiconductor industry, the evaluation of quantum properties at cryogenic temperatures and the neutral single-atomic vacancy concentration leading to these properties remains to be understood properly. This is also true for diamonds. The determination of residual atomic vacancies at the few ppb level, which were previously unattain-

able (and overlooked) optically, is critical to improve the coherence time of quantum-information devices when downsizing quantum circuits in the future. Therefore, it is crucial to investigate the properties and establish an evaluation procedure for the low vacancy concentration in diamonds for quantum applications.

We used three commercially available synthetic diamond species grown by HPHT synthesis (Sample 1 and 2) and CVD (Sample 3) for our ultrasonic measurements presented here (see SM [20] for experimental details). The temperature dependence of the elastic constant C_{44} at zero magnetic field is shown in Figs. 2(a) and 2(c) for single-crystalline HPHT type-IIa diamond (Sample 1). C_{44} gradually hardens down to ~ 1 K [as shown in the inset of Fig. 2(c)], which is a general behavior of solids owing to the anharmonicity of acoustic phonons. This change is consistent with previously reported temperature dependences of the sound velocity of transverse ultrasonic waves down to ~ 10 K [33–35]. Notably, to the best of our knowledge, no previous work has yet studied the elastic constants below 10 K. The low-temperature region of C_{44} exhibits 125 ppm softening from 1 K down to 20 mK. In analogy to the interpretation for a similar softening observed in Si, the molecular orbitals of the neutral single vacancies remain at a triple-degenerated quantum state at least down to these temperatures. These results evidence that the local cubic T_d symmetry around a single neutral vacancy V_0 in diamond also remains preserved. In the Sec. 10 of the SM [20], we elaborate the reasons why the effect of NV^- (as shown in Fig. 1), NV_0 (with electrons removed from NV^-), large multi-atom vacancy V_n clusters [36, 37], P_1 centers (neutral single-substitutional nitrogen) [38], and nuclear spins have no effect on the elastic softening.

The solid red line in Fig. 2(a) is the result of calculations based on the equation $C_{\Gamma_5} = C_{\Gamma_5}^{bk}(T - T_C)/(T - \Theta)$ (for details, see SM [20]). The fit yields $T_C = -260.196$ mK, $\Theta = -260.242$ mK, and $\Delta_{JT} = T_C - \Theta = 0.046$ mK. The dashed line represents the phenomenological fit for the background contribution $C_{\Gamma_5}^{bk} = C_{\Gamma_5}^0 - s/\{\exp(t/T) - 1\}$ [39], with $C_{\Gamma_5}^0 = 5.69923 \times 10^{11}$ J m $^{-3}$, $s = -4.681226 \times 10^7$, and $t = 2.941652$. The negative value of Θ indicates an antiferro-type inter-vacancy interaction for the charge state of the vacancy V_0 . The negative value of T_C suggests quadrupolar fluctuations associated with the triple-degenerate quantum state even at the lowest temperature of ~ 20 mK. This result further proves that the cubic site symmetry T_d at the vacancy site is preserved in the investigated diamond material, *i.e.*, the local distortion owing to the static Jahn-Teller effect is irrelevant for this diamond with low vacancy concentration.

From optical measurements [25, 40, 41] on irradiated diamonds [42], an E (vibronic) ground state has been proposed for V_0 [43, 44]. This ground state cannot explain the present elastic softening in C_{44} . Another experi-

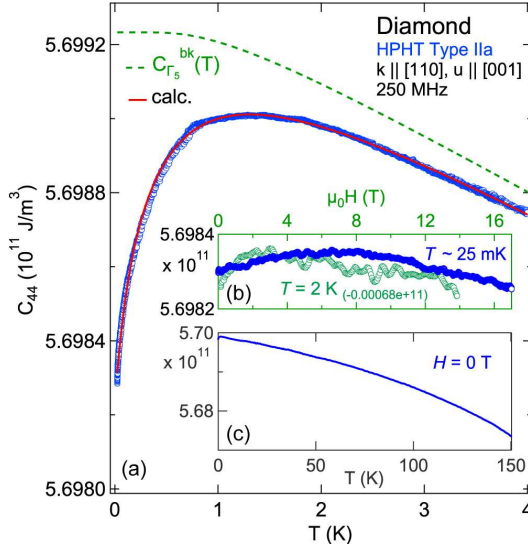


FIG. 2. (a) Temperature dependence of the elastic constant C_{44} for single-crystalline synthetic HPHT diamond (type IIa) below 4 K at zero magnetic field compared to calculations (solid red curve) based on the orbital analogue of the Curie-Weiss law (see text). The green dashed line represents the background term C_{44}^{bk} owing to phonons uncoupled to the electronic system. (b) Magnetic-field dependence of C_{44} at 25 mK (blue) and 2 K (green) with shifted offset for the 2 K data. The magnetic field is applied along the [001] direction. (c) Temperature dependence of the elastic constant C_{44} for a wide temperature region up to 150 K.

ment on non-irradiated diamond using circular-polarized light recently revealed an A_1 symmetry for the ground state of the neutral single atomic vacancy [45]. Therefore, we argue that the ground state of the neutral single vacancy (V_0) in the non-irradiated diamond has A_1 symmetry. A consistent picture of the quantum ground state has not been unambiguously established yet, see Sec. 9 in the SM [20].

Figure 1 illustrates schematically the crystal structure of diamond (top) and the two types of dangling bonds created by atomic vacancies (middle). There are eight atoms in the unit cell, and the atomic positions of the $8a$ sites are $[0,0,0]$, $[\frac{1}{2}, \frac{1}{2}, 0]$, $[0, \frac{1}{2}, \frac{1}{2}]$, and $[\frac{1}{2}, 0, \frac{1}{2}]$. The $8b$ sites are translationally shifted by $[\frac{1}{4}, \frac{1}{4}, \frac{1}{4}]$ from those. Both exhibit the same site-symmetry T_d , where the spatial inversion symmetry is broken. Adjacent atoms are located at the vertex and center of the tetrahedron and belong to the crystallographically different $8a$ and $8b$ sites, respectively. As the spin-orbit interaction is small in diamond, we do not consider the effect of odd-parity multipoles but only that of even-parity ones [46]. When the molecular orbitals are placed in an electrostatic potential of T_d site symmetry, it results in an energy splitting between a non-degenerate bonding orbital, called a_1 singlet ($E - 3\gamma$) and 3-fold degenerate antibonding orbitals, called t_2 triplet ($E + \gamma$), as shown schematically at the bottom of Fig. 1

(for corresponding wave functions, see Sec. 5 in the SM [20]).

Moreover, the charge state of the atomic vacancy is determined by the site symmetry of the vacancy and number of electrons in the orbital. To describe the quantum ground state of a single neutral vacancy V_0 , we consider a quantum state in which two electrons occupy the a_1 singlet and the other two enter the t_2 triplet state. The product space in the t_2 triplet state of the T_d group is irreducibly decomposed as $(t_2 \otimes t_2) = A_1 \oplus E \oplus T_1 \oplus T_2$, including 9 degrees of freedom. At $S = 0$, the electric quadrupole degrees of freedom belonging only to the E and T_2 symmetry are active. The quadrupole degrees of freedom that contribute to the softening of C_{44} are O_{xy} , O_{xz} , and O_{yz} , which exhibit T_2 symmetry. The specific matrix elements of the electric quadrupoles can be represented using a Gell-Mann matrix and generated by applying the rotation group $SU(3)$ to the three-dimensional representation T_2 [27].

Further, in an NV center the vacancy site exhibits lower C_{3v} symmetry, because of a local symmetry reduction owing to the substitution of one C site by N. Therefore, the sp^3 orbital splits into two a_1 singlets and one e doublet [47, 48]. When the nitrogen donor in the substituted position provides the carrier for the valence -1, the NV center is negatively charged (NV^-). According to Hund's first rule, the ground state adopts the highest value of total spin S , which is consistent with the Pauli exclusion principle. The six electrons occupy the a_1 singlets and the x and y orbits of the e doublet to satisfy the condition that all wavefunctions are antisymmetric. Therefore, the ground state of NV^- results in an $S = 1$ state as shown Fig. 1. However, no electric quadrupole degrees of freedom exist in the product space of $(e \otimes e)$ with $S = 1$. Therefore, the e orbitals of NV^- do not contribute to the softening of C_{44} .

We estimate the vacancy concentration using the relation $N = \Delta_{JT} C_T^0 / \delta_T^0$ for the acoustic mode C_{44} , which was used to analyze the vacancy concentration in Si as well [27]. Here, N denotes the atomic vacancy concentration, Δ_{JT} the Jahn-Teller energy, and δ_T^0 the deformation binding energy. The softening of Czochralski (CZ)-grown Si starts below approximately 10 K, whereas that of diamond starts below about 1 K. In line with that, Δ_{JT} obtained from the present analysis for diamond is approximately one-tenth of that of Si. Our experiments yield the parameters Δ_{JT} and C_T^0 , but not δ_T^0 , which is unknown for diamond. As a first try, we assume the same value as for Si, *i.e.*, $\delta_T^0 \sim 2.28 \times 10^5$ K [29], despite the difference in the dielectric constant, melting temperature, and lattice constant [27]. The estimated neutral single-atomic vacancy concentration for the present sample of type-IIa diamond is ~ 0.2 ppb, exhibiting the same order of magnitude as that for CZ-grown Si, namely ~ 0.11 ppb. Notably, the large difference in the elastic constants, which is seven times larger for diamond than for Si, was

also considered in these calculations. Δ_{JT} and C_{Γ}^0 have an error of approximately 5%. Therefore, the parameter δ_{Γ}^0 is dominant in determining the order of N .

If we use the formation energy 8.373 eV of the neutral vacancy, recently estimated by ab-initio calculation [44], we obtain a vacancy concentrations of 0.5 ppb, which is close to our above estimate of 0.02 ppb. Of course, precise values are not meaningful, but we can estimate the order of magnitude depending on how the binding constant is considered. However, there is no doubt that the vacancy concentration is definitely in the sub-ppb level. It would be highly desirable to refine the unknown parameter δ_{Γ}^0 by theory and ultrasonic experiments using diamonds with known higher vacancy concentration, which can be controlled by irradiation.

According to the theory proposed in a previous study for Si [20, 27], the deformation binding energy can be expressed by a relationship using the quadrupole-strain coupling constant g_{Γ} . This coupling constant is proportional to the effective charge Z^* and the square of the effective radius a^* of the vacancy orbital (see SM) [20, 49]. In case of Si, a triple-degenerate vacancy state within the band gap can be significantly extended over a large distance of ~ 20 Å around the vacancy site [50]. In conjunction with such theoretical predictions, ultrasonic experiments on boron-doped Si have estimated the value of the strain coupling constant $g_{\Gamma 5}$, corresponding to Γ_5 symmetry, to be approximately 2.8×10^5 K [29]. Even if the atomic vacancies are diluted, the spatially extended molecular orbitals of Si atomic vacancies contribute to the reciprocal temperature dependence of the quadrupole susceptibility, which results in the elastic softening at low temperatures. Importantly, the substantial value of $g_{\Gamma 5}$ allows for the detection of atomic vacancies at the sub-ppb level by use of ultrasound techniques.

Further, we investigated the elastic response for other diamonds grown by different methods. Figure 3 shows the temperature dependence of C_{44} for three different types of diamonds. Sample 1 is the type-IIa HPHT diamond with data already shown in Fig. 2. Sample 2 is also a type-IIa diamond grown by CVD. Sample 3 is a HPHT yellow diamond of type Ib that presumably contains numerous nitrogen impurities. Sample 1 and 2 show a nearly identical low-temperature softening within the resolution of the present measurements. The data for Sample 2 are somewhat noisy because of the small sample thickness. The softening in Sample 3 (type-Ib HPHT) is only approximately 1/3 of that of the Samples 1 and 2 (type IIa). This presumably is attributed to the neutralization of atomic vacancies by nitrogen doping. It is reasonable to assume that the concentration of neutral single vacancies in Sample 3 is less than in Samples 1 and 2 (type IIa). The inset of Fig. 3 shows data up to 100 K on a logarithmic temperature axis. Notably, the softening in Samples 2 and 3 is robust to external magnetic fields up to 14.0-16.5 T, similar as found for Sample

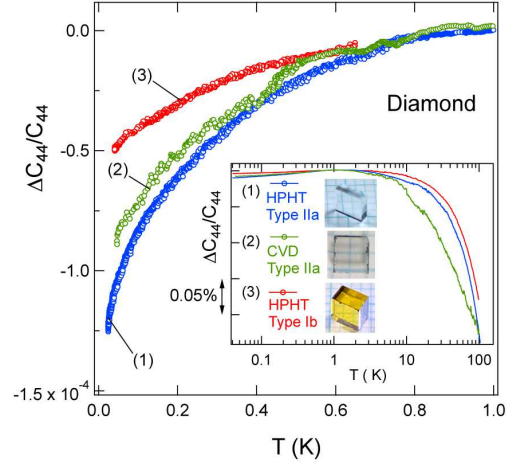


FIG. 3. Comparison of the elastic softening of C_{44} for three different types of diamond. (1: blue symbols) HPHT type IIa (see also Fig. 2), (2: green symbols) CVD type IIa, and (3: red symbols) HPHT type Ib. The relative variation in $\Delta C_{44}/C_{44}$ was normalized at 1 K. The inset shows results up to 100 K in a semilogarithmic scale. Photographs of the samples used for the measurements are shown as well.

1 [20].

In summary, our ultrasound studies clearly reveal the presence of neutral single vacancies on the ppb level in all three diamond types investigated. In particular, we have uncovered that CVD diamonds, which are widely used for optical measurements in quantum technologies, also have atomic vacancies on the ppb level comparable to HPHT-grown diamonds. This result should be considered for future downsizing and removal of spin-noise sources in NV centers used as quantum devices. Importantly, the present study focused on atomic vacancies formed spontaneously during single-crystal growth, excluding those formed by neutron- or electron-beam irradiation. These results are of particular importance for researchers utilizing such diamonds in various fields, such as in quantum information, biological sensing, and power devices. Furthermore, our findings provide a novel perspective for studying atomic vacancies in diamonds. Further investigations of the elastic response of various types of diamonds at cryogenic temperature are required to explore in detail the underlying physics of diamond vacancies with respect to possible technological applications.

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